



2SK4124 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		500	V
Gate-to-Source Voltage	V_{GSS}		± 30	V
Drain Current (DC)	I_D		20	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	60	A
Allowable Power Dissipation	P_D		2.5	W
		$T_c=25^\circ\text{C}$ (SANYO's ideal heat dissipation condition)*1	170	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *2	E_{AS}		124	mJ
Avalanche Current *3	I_{AV}		20	A

*1 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*2 $V_{DD}=99\text{V}$, $L=500\mu\text{H}$, $I_{AV}=20\text{A}$

*3 $L \leq 500\mu\text{H}$, single pulse

Marking : K4124

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2SK4124

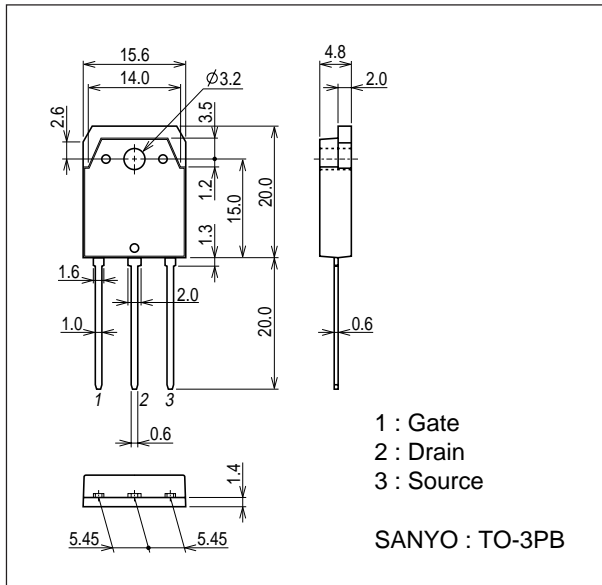
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	500			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=400V, V_{GS}=0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=10A$	4.9	9.7		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=8A, V_{GS}=10V$		0.33	0.43	Ω
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		1200		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		250		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		55		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		26.5		ns
Rise Time	t_r	See specified Test Circuit.		95		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		145		ns
Fall Time	t_f	See specified Test Circuit.		58		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=20A$		46.6		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=20A$		8.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=20A$		27.3		nC
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$		1.0	1.3	V

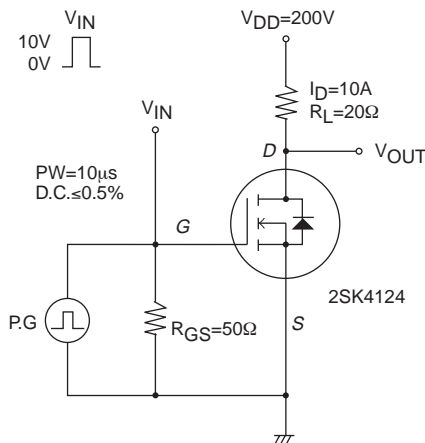
Package Dimensions

unit : mm (typ)

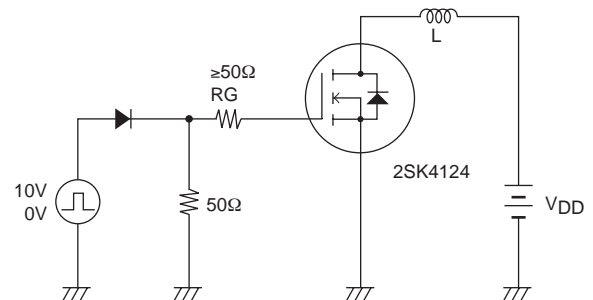
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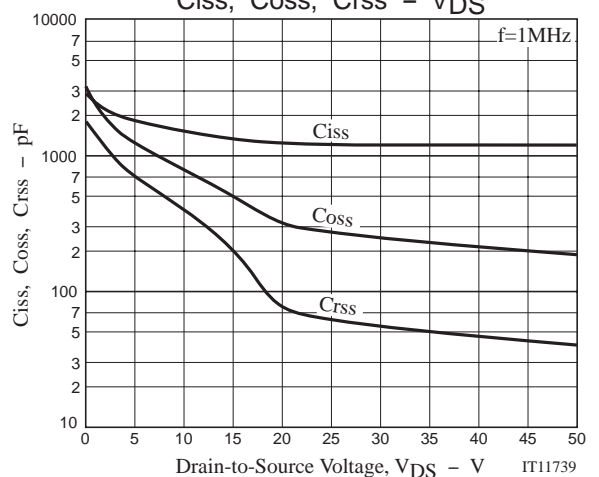
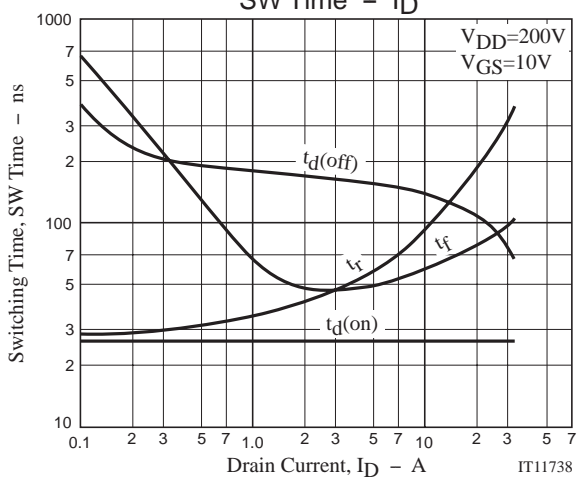
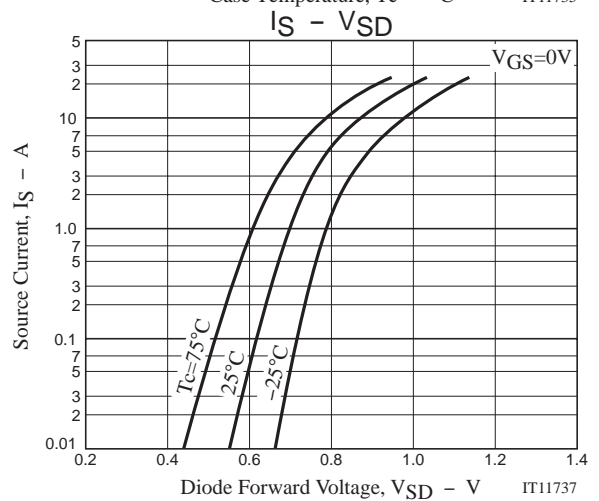
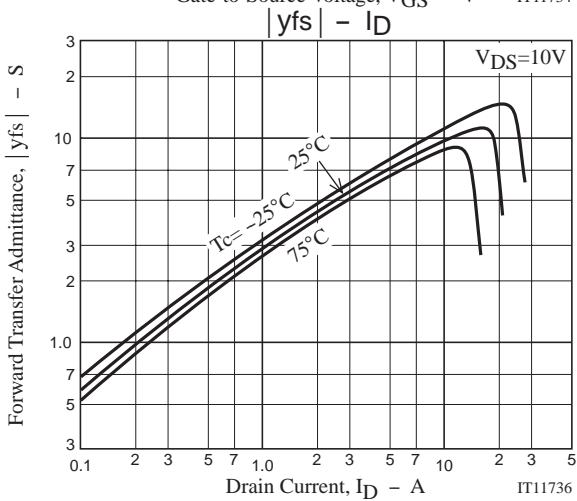
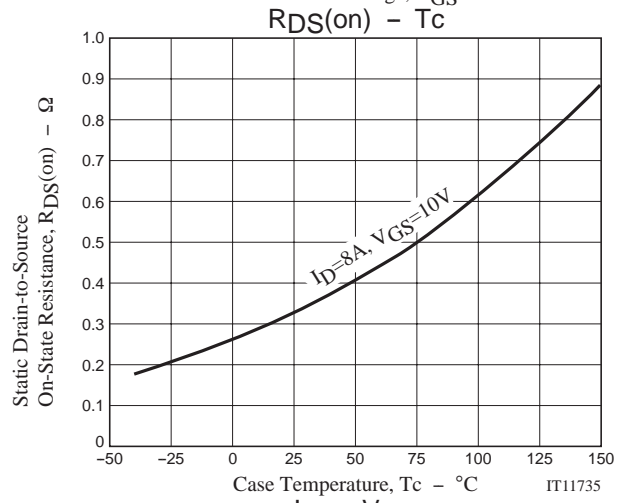
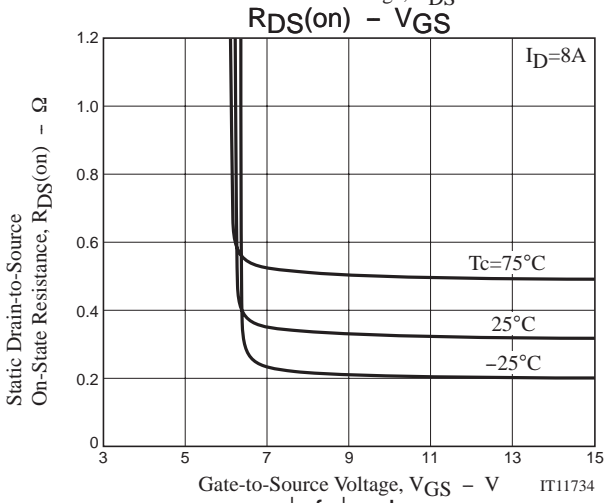
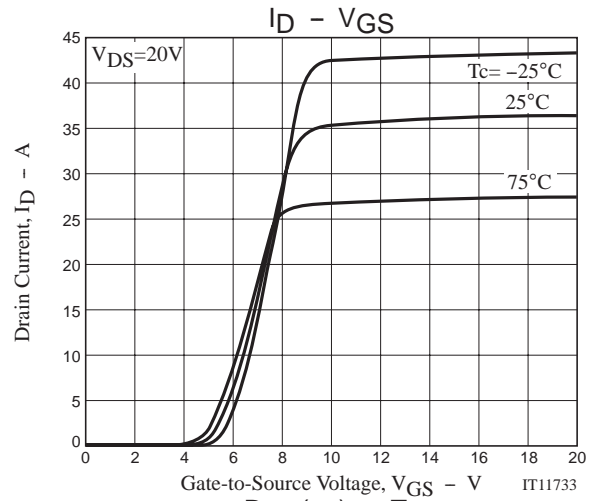
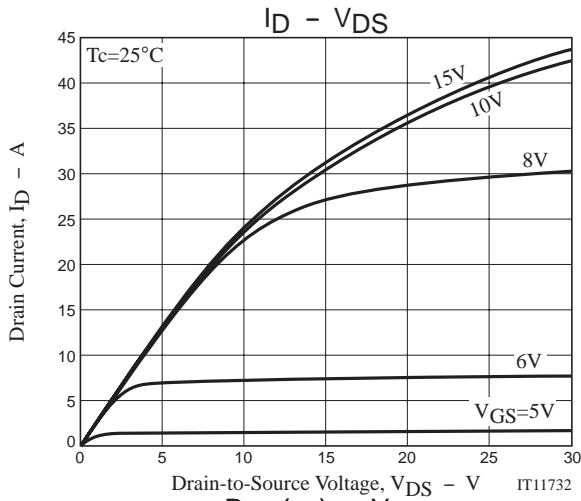
Switching Time Test Circuit

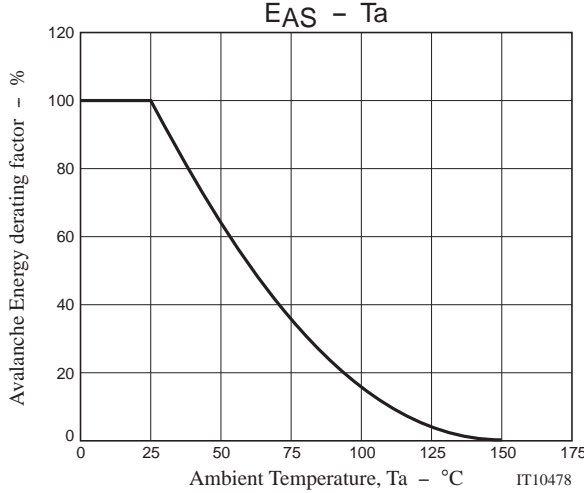
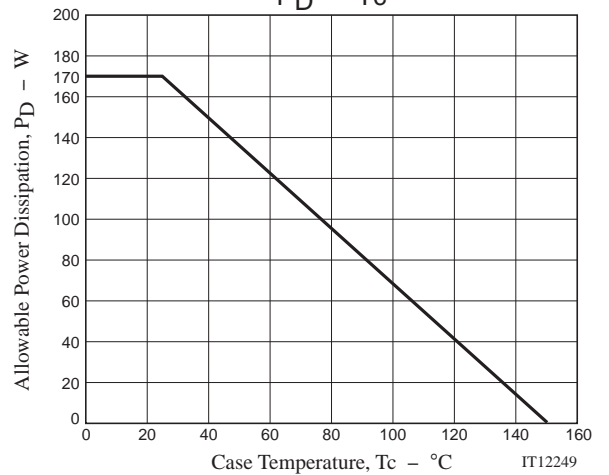
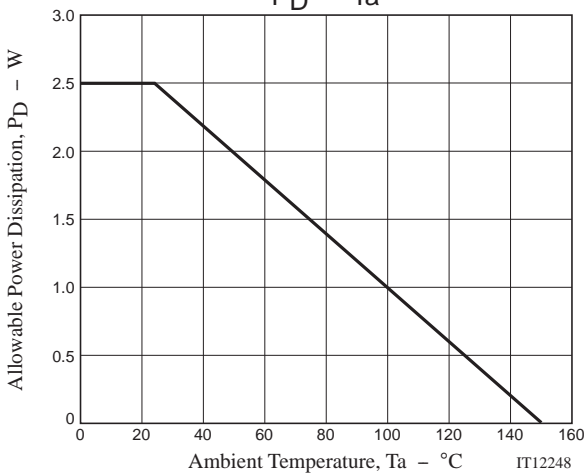
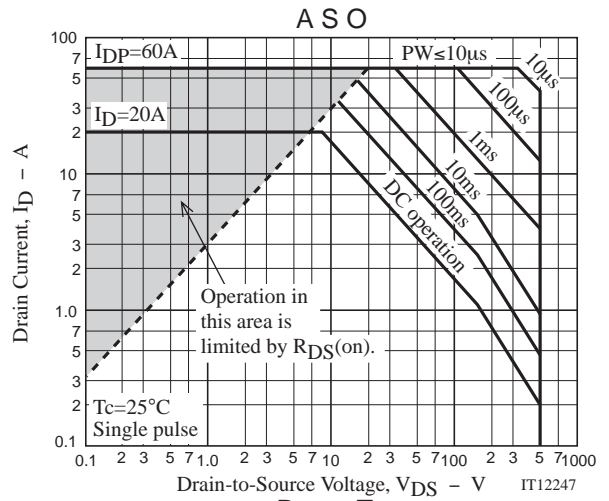
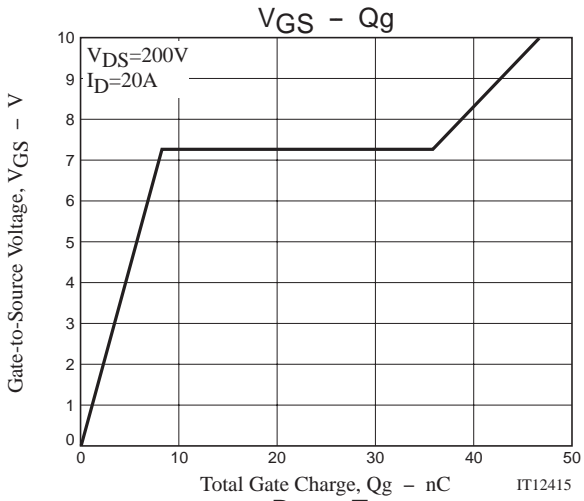


Avalanche Resistance Test Circuit



2SK4124





Note on usage : Since the 2SK4124 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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